

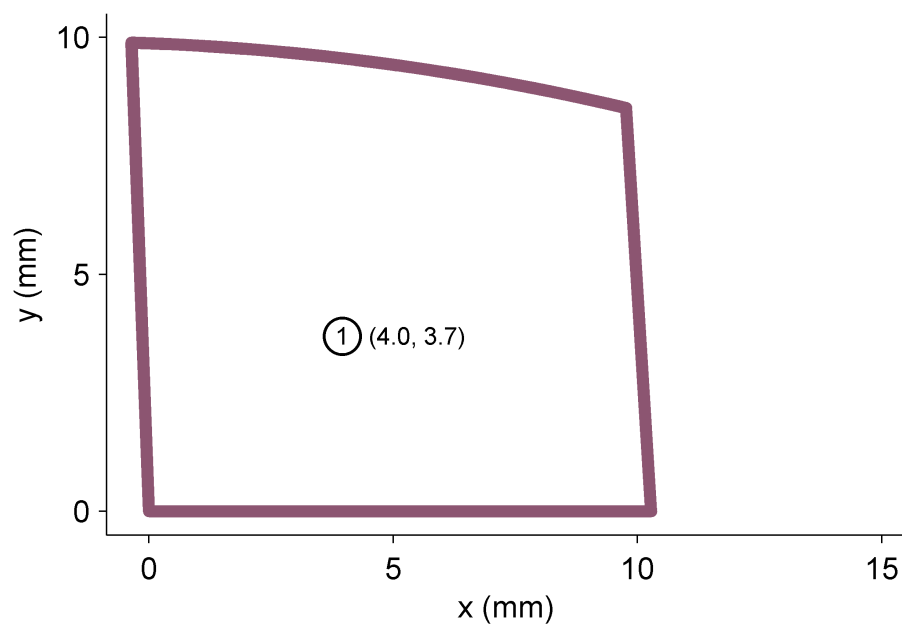


Sample S5130 Datasheet

Parent Wafer

Supplier	IDB Technologies Ltd.
Diameter	100mm
Si Orientation	<100>
Si Thickness	525 μm
Si Doping	N-type, arsenic
Resistivity	0.001-0.010 Ωcm
Oxide	90 nm dry thermal oxide

Substrate Map



Flake 1 of 1: x=4.0mm, y=3.7mm, mono-, bi- and trilayer regions